

Coulomb blockade thermometry using a two-dimensional array of tunnel junctions

Tobias Bergsten, Tord Claeson and Per Delsing

Department of Microelectronics and Nanoscience, Chalmers University of Technology

and Göteborg University, SE-412 96 Göteborg, Suède

We have measured current-voltage characteristics of two-dimensional arrays of small tunnel junctions at temperatures from 1.5 K to 4.2 K. This corresponds to thermal energies larger than the charging energy. We show that 2D-arrays can be used as primary thermometers in the same way as 1D-arrays, and even have some advantages over 1D-arrays. We have carried out Monte Carlo simulations, which agree with our experimental results.

I. Introduction

Thermometers can be divided into two categories: primary and secondary ones. The former do not have to be calibrated, but are generally slow and expensive, and are therefore mainly used for calibration purposes. Secondary thermometers are, on the other hand, usually cheap and fast, but they need to be calibrated against a known temperature scale, i.e. a primary thermometer or a scale which can be traced to one. The vast majority of thermometers used for routine measurements are secondary thermometers.

Recently, a new primary thermometry method, the Coulomb blockade thermometry (CBT), was demonstrated by Pekola *et al.*[1] It is based on the charging effects in one-dimensional (1D) arrays of very small tunnel junctions. When the charging energy of the junctions, $E_C = e^2/2C$, is greater than or of the order of the thermal energy, $k_B T$, the finite charge of the electron gives rise to a decreased differential electrical conductivity at low voltages (C is the tunnel junction capacitance and T is the temperature). This is called the Coulomb blockade of tunnelling [2, 3]. The Coulomb blockade shows up as a bell-shaped dip (figure 1) when the differential conductance, $\frac{dI}{dV}$, is plotted against the bias voltage, V . The depth of this dip is inversely proportional and the half-width is directly proportional to the temperature. Interestingly, the half-width depends only on the temperature, T , and natural constants, which makes it useful for primary thermometry. This method has the advantage over other primary methods used at cryogenic temperatures in that it is both faster and cheaper, furthermore the physical size of the thermometer can be made less than a mm. The depth of the conductance dip depends on the tunnel junction capacitance, C , as well. Pekola *et al.* have demonstrated that this method can give an accuracy in temperature of at least 0.5% and they have used it successfully in the range from 20 mK to 30 K, more than three

orders of magnitude, which is a large range for a primary thermometer.

In this paper we show experimental data for a CBT consisting of a two-dimensional (2D) array of tunnel junctions, rather than the 1D-arrays demonstrated by the group of Pekola *et al.* [1, 4, 12] One practical problem with 1D-arrays of tunnel junctions is that they are dependent on every junction to function properly, like a chain is only as strong as its weakest link. So if one junction is damaged, ages rapidly or simply is bad from the beginning, the array might be unusable or at least its performance will be degraded. One way to reduce this degradation due to bad junctions is to connect several arrays in parallel, thus reducing the error to the order of $1/M$, where M is the number of arrays. Even better is to make a 2D-array, where the metal islands are connected with tunnel junctions both in parallel and in series. The current would then simply pass around any broken junctions. This reduces the error due to a broken junction to the order $1/MN$, where M and N are the number of junctions in parallel and in series respectively. (The resistance of an array of resistors increases with a factor of approximately $2/MN$ if one resistor is removed.)

We have measured current-voltage characteristics on a 2D array of tunnel junctions at temperatures from 1.5 K to 4.2 K in a pumped ^4He cryostat. Using the formulas derived for 1D-arrays we have calculated the temperatures from these IV-curves and compared them with temperatures calculated from the pressure of the He gas in the cryostat. The correspondence is very good.

We have also made Monte-Carlo simulations of 1D- and 2D-arrays and these simulations show that the tunnel junction capacitance C which is used in the equations for 1D-arrays should be replaced in the 2D case by an effective capacitance C_{eff} which is higher than the real capacitance.

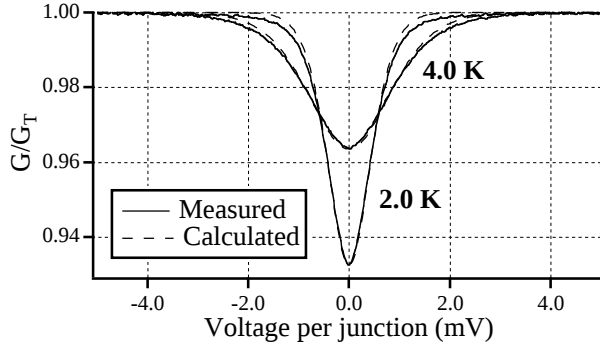


FIG. 1. The differential conductance as a function of bias voltage shows a bell-shaped dip around zero voltage. These measurements were made on a 256×256 junction 2D-array with a resistance of $17 \text{ k}\Omega$ and an effective capacitance of 2 fF . The calculated curves were calculated with higher order corrections [4].

II. Theory

The differential conductance G of a 1D-array of N junctions has been calculated theoretically [1] to first order in the limit $E_C \ll k_B T$. For arrays where all junctions have the same resistance and capacitance and negligible capacitance to ground, the result is

$$\frac{G}{G_T} = 1 - u_N g(v_N), \quad (1)$$

$$g(x) = \frac{x \sinh(x) - 4 \sinh^2 \frac{x}{2}}{8 \sinh^4 \frac{x}{2}}$$

where the parameters u_N and v_N are defined as

$$u_N = 2 \frac{N-1}{N} \frac{E_C}{k_B T} = 2 \frac{E_{C,\text{eff}}}{k_B T}, \quad (2)$$

$$v_N = \frac{eV}{N k_B T}. \quad (3)$$

G_T is the differential conductance at voltages far above the Coulomb blockade. The effective charging energy, $E_{C,\text{eff}}$ is defined similarly to the usual charging energy, except the physical capacitance is replaced with the effective capacitance (which in a 1D-array with negligible capacitance to ground is $C_{\text{eff}} = \frac{N}{N-1} C$).

The half-width $V_{\frac{1}{2}}$ of the resulting conductance dip depends only on N and T :

$$eV_{\frac{1}{2}} = 5.439 N k_B T. \quad (4)$$

The depth $\frac{\Delta G}{G_T} = \frac{1}{6} u_N$ of the conductance dip also depends on the effective capacitance C_{eff} of the junctions.

At low temperatures ($k_B T \approx E_C$) higher order corrections should be included [4]. This gives a correction to the halfwidth in equation (4), which is independent of temperature:

$$eV_{\frac{1}{2}} = 5.439 N k_B T \left(1 + 0.3921 \frac{\Delta G}{G_T} \right) \quad (5)$$

$$= 5.439 N k_B T + 0.7108 N E_{C,\text{eff}}.$$

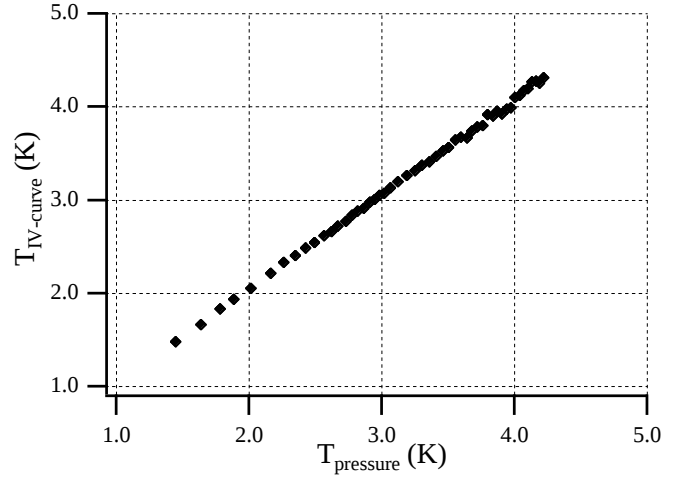


FIG. 2. Comparison between the temperature calculated from the half-width of the Coulomb blockade in the IV-curve and the temperature calculated from the ^4He equilibrium pressure.

III. Sample parameters

The measured array consisted of 256×256 tunnel junctions in a square pattern with a side of $200 \mu\text{m}$ and the area of the overlap junctions was approximately 150 nm squared. The tunnel junctions were made of aluminium with a tunnel barrier consisting of aluminium oxide, AlO_x , fabricated with standard shadow evaporation technique [7, 8]. The junctions had a tunnelling resistance of $17 \text{ k}\Omega$ and a capacitance of 1.1 fF which means E_C/k_B was 0.85 K . The capacitance was calculated from the offset voltage, $V_{\text{off}} = 9.0 \text{ mV}$, using the offset analysis method described in ref [5]. We have furthermore assumed that the offset voltage of a 2D-array of tunnel junctions is $V_{\text{off}} = eN/4C$ [6].

IV. Experimental setup

The measurements were carried out in a pumped ^4He cryostat which has a temperature range from 4.2 K down to approximately 1.2 K . A custom built biasing and amplification box fed the source signal to the sample and amplified the current and voltage signals, which were measured with two Keithley 2000 multimeters. A computer controlled Keithley 213 voltage source was used for the voltage sweep. The ^4He bath pressure was measured by a Wallace & Tiernan FA129 analog pressure meter which was connected directly to the pumped helium space.

V. Results

We measured IV-curves at 50 different temperature points and differentiated them numerically. Using equation 5 we calculated the temperature and compared it with the temperature calculated from the ^4He equilibrium pressure in the He bath, using the definition of ITS-90 [9]. As can be seen in figure 2 the two temperatures are almost the same, but not quite. The temperature from the IV-curve

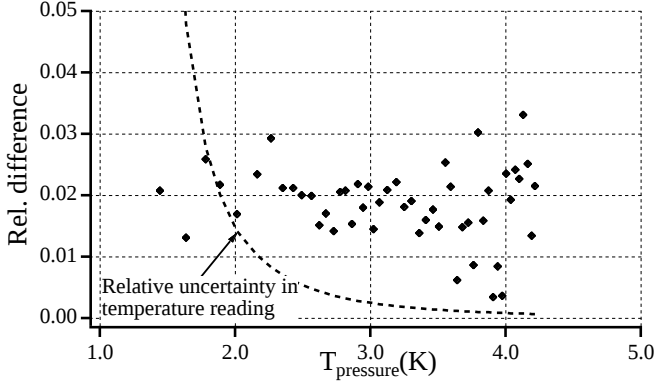


FIG. 3. The relative difference between the temperature calculated from the IV-curve and from the ^4He pressure. There is a systematic difference of around 2%. As a comparison the uncertainty from the pressure reading is included, but it can't account for all the difference in temperature.

is consistently slightly higher than the temperature from the ^4He pressure.

The difference is clearer if we plot the relative difference, *i.e.* $(T_{IV} - T_{pres})/T_{pres}$ (figure 3). We see that there is a positive difference of 1-3% in all the measurements. The uncertainty in the pressure readings was estimated to about 1 Torr and the resulting temperature uncertainty is also shown in figure 3. While it may account for some of the spread, it can not explain the systematic difference of about 2%. One possible explanation could be that the IV-curves were measured quite rapidly one after the other, and perhaps the sample did not quite cool down at each temperature before the measurement was made.

We have made Monte Carlo simulations of one- and two-dimensional tunnel junction arrays with a program package called SIMON [10] which is intended for simulations of circuits with very small tunnel junctions. Because this method turned out to be very time-consuming, we settled for quite small arrays, only three junctions in series and two in parallel. Both 1D and 2D arrays behaved according to theory, except that in the 2D case the capacitance in equation 2 was not the actual capacitance of the tunnel junctions, but an effective capacitance C_{eff} which was approximately 1.4 times the actual value in the 3×2 junction array. This is not surprising, though, since two islands are not only connected via the junction between them, but also via the other islands in the array. In an infinite 2D array the capacitance between two neighbouring islands is exactly twice the capacitance of the tunnel junctions, and this is the reason that the offset voltage is a factor of two lower in a 2D-array compared to a 1D-array [6]. By calculating the effective capacitance from $\frac{\Delta G}{G_T}$ we get $C_{\text{eff}} \approx 2.2 fF$, which is twice the capacitance calculated from the offset voltage, as expected.

An important property of the 2D-array is that it can be fabricated with lower resistance than a 1D-array, even if it contains many junctions in series. This means that the measurement can be done faster and the measurement error is lower. When deducing the temperature from the half-width of the conductance vs voltage curve, the uncer-

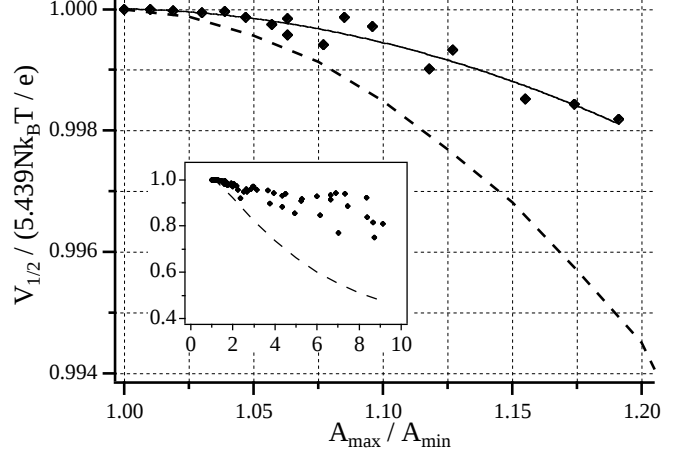


FIG. 4. The simulated half-width voltage, scaled by the ideal value, plotted against $A_{\text{max}}/A_{\text{min}}$ (dots) for a 5×5 junction array. A_{max} and A_{min} are the maximum and minimum junction areas respectively. The dashed lines are the corresponding results for 1D-arrays by Hirvi *et al.*[11], and the solid line is a quadratic fit to the simulated values, to compare with the quadratic dependence in the 1D-array. It is clear that 2D-arrays are less affected by variations in the tunnel junction areas than 1D-arrays, both at moderate (big figure) and large (inset) variations. Larger arrays give essentially the same result.

tainty in T depends both on the uncertainty in G and in V . The measurement uncertainty can be written

$$\frac{\delta T}{T} = \frac{4.60 \frac{\delta G}{G}}{u_N} + \frac{\delta V}{V_{\frac{1}{2}}}, \quad (6)$$

$$\frac{\delta G}{G} = \frac{\delta I}{\Delta I} + \frac{\delta V}{\Delta V} + \frac{u_N}{720} \left(\frac{e \Delta V}{N k_B T} \right)^2 \quad (7)$$

where δI and δV are the current and voltage uncertainties respectively, given by the array resistance and temperature, and the amplifier noise. ΔI and ΔV are the intervals used for the numerical differentiation of the IV-curves or, if lock-in measurements are used, the modulation amplitude. Note that $\Delta I = G_{\frac{1}{2}} \Delta V$ where $G_{\frac{1}{2}}$ is the differential conductance at the half-width voltage. The last term in eq. 7 is the maximum differentiation error. Equation 7 has a minimum with respect to ΔV and we can choose ΔV (in our case approximately 5 % of $V_{\frac{1}{2}}$) to minimise the total error:

$$\frac{\delta T}{T} = 0.971 \left(\frac{R_T \frac{\delta I}{M} + \frac{\delta V}{N}}{e/C_{\text{eff}}} \right)^{2/3} + \frac{\delta V}{V_{\frac{1}{2}}}. \quad (8)$$

R_T is the tunnelling resistance per junction at the half-width voltage. Note that the uncertainty decreases both with increasing N and M .

Now we want to compare the measurement uncertainty of a 1D- and a 2D-array. In this example we use a typical 1D-array of 30 junctions (typical because this is the approximate size used by Pekola *et al.*), each junction with an effective capacitance of 2 fF and a resistance of 20 k Ω .

For the 2D-array we assume 256×256 junctions and the same junction parameters. The temperature is 4 K. For the measurement we assume AD743 operational amplifiers at the input stage, because they have low voltage noise. The resulting uncertainty is $1.2 \cdot 10^{-3}$ for the 1D-array and $0.22 \cdot 10^{-3}$ for the 2D-array, *i.e.* five times lower in the 2D case. One might argue that we would get the same effect if we fabricated 256 parallel 1D-arrays with 256 junctions each, but then we might just as well make it 2D, for the sake of robustness, as discussed earlier.

Another important issue is the tolerance to variations in the tunnel junction properties. Since no fabrication process is perfect, small variations can always be expected and in general, the smaller the structures, the bigger are the relative differences. Hirvi *et al.* have calculated the measurement error which can be expected in a 1D-array at different inhomogeneities [11]. We have simulated a 5×5 junction 2D-array with random distributions of tunnel junction areas and plotted the resulting half-width voltage $V_{\frac{1}{2}}$ against the parameter $A_{\max}/A_{\min}$, where $A_{\max}$ and $A_{\min}$ are the maximum and minimum junction areas respectively (figure 4). Increasing the number of junctions give essentially the same result. We have assumed that $R_{i,j}C_{i,j} = \text{constant}$ for all junctions, which follows from uniform tunnel barriers. It is clear from the figure that the 2D-array is much less affected by variations in the junction areas than 1D-arrays. For example, at a 10% spread ($A_{\max}/A_{\min} = 1.10$) the error in a 1D-array is $\approx 0.15\%$, while in a square 2D-array it is $\approx 0.05\%$. It should be noted that even a $2 \times N$ -array is significantly better than a 1D-array in this respect, at 10% spread the error is $\approx 0.08\%$.

VI. Conclusions

We have shown that a 2D-array of tunnel junctions can be used as a primary thermometer in the same manner as 1D-arrays demonstrated earlier. 2D-arrays have certain advantages over 1D-arrays for this application, namely the robustness to damage of individual tunnel junctions, higher tolerance to variations in tunnel junction properties, lower signal noise and lower resistance which enables faster measurement. This should make them more suitable for temperature measurements at temperatures above a few hundred mK where the electron heating effect is not a big problem. At lower temperatures 1D-arrays are probably better, since the topology of 1D-arrays allow big cooling fins to be attached to the metal islands of the array, and this will improve the thermalisation of the electron system [12].

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